

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

F18920030221 US1

Application Number

10/605 227

Applicant(s)

K. Chong, et al

Filing Date

9/16/2003

Group Art Unit

2822

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
		4,952,524	8-28-90	Lee, et al.			

## U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
		US 2002/0086472	7-4-02	Roberds, et al.			

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		JP64-76755	03-1989	Japan				

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained SI N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

EXAMINER

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		4,958,213	9-18-90	Eklund, et al.			
		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
		5,108,843	4-28-92	Ohtaka, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeh, et al.			
		US 2003/0040158 A1	2-27-03	Saitoh			

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**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)

		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

EXAMINER

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		5,134,085	7-28-92	Gilgen, et al.			
		5,310,446	5-10-94	Konishi, et al.			
		5,354,695	10-11-94	Leedy			
		5,371,399	12-6-94	Burroughes, et al.			
		5,391,510	2-21-95	Hsu, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2003/0057184 A1	3-27-03	Yu, et al.			
		US 2003/0067035 A1	4-10-03	Tews, et al.			

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**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
		5,565,697	10-15-96	Asakawa, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

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		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

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		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
		5,679,965	10-21-97	Schetzina			

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		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and Its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.
		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

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## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leedy			
		5,861,651	1-19-99	Brasen, et al.			
		5,880,040	3-9-99	Sun, et al.			
		5,940,716	8-17-99	Jin, et al.			

## U.S. PATENT APPLICATION PUBLICATIONS

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## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.
		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Saki			
		5,989,978	11-23-99	Peidous			
		6,008,126	12-28-99	Leedy			

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## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.
		H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

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		6,025,280	2-15-00	Brady, et al.			
		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
		6,107,143	8-22-00	Park, et al.			

## U.S. PATENT APPLICATION PUBLICATIONS

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## OTHER DOCUMENTS

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		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.
		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistor for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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		6,117,722	9-12-00	Wuu, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
		6,228,694	5-8-01	Doyle, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

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		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
		6,274,444	8-14-01	Wang			

## U.S. PATENT APPLICATION PUBLICATIONS

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		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
		6,361,885	3-26-02	Chou			

**U.S. PATENT APPLICATION PUBLICATIONS**

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		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
		6,406,973	6-18-02	Lee			

**U.S. PATENT APPLICATION PUBLICATIONS**

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		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
		6,498,358	12-24-02	Lach, et al.			

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		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
		6,531,369	3-11-03	Ozkan, et al.			

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		6,531,740	3-11-03	Bosco, et al.			
		6,621,392	9-16-03	Volant, et al.			
		6,635,506	10-21-03	Volant, et al.			

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